

Listing Of Claims

Claims 1-33 (Canceled)

34. (previously presented) A method for fabricating an interconnect for engaging a bumped contact on a semiconductor component comprising:

providing a substrate;

forming a plurality of leads on the substrate configured to electrically engage and support the bumped contact;

forming a recess in the substrate such that the leads cantilever over the recess and are configured for movement within the recess during electrical engagement of the bumped contact; and

forming an outer layer on each lead configured to provide a non-bonding surface for the bumped contact.

35. (previously presented) The method of claim 34 wherein the outer layer comprises a material selected from the group consisting of Ti, TiSi_2 , Al and a conductive polymer.

Claims 36-37 (Withdrawn)

38. (previously presented) The method of claim 34 further comprising forming at least one blade on each lead configured to penetrate the bumped contact.

39. (previously presented) A method for fabricating an interconnect for engaging a bumped contact on a semiconductor component comprising:

providing a substrate;

forming a metal layer on the substrate;

forming a plurality of blades in the metal layer configured to penetrate the bumped contact;

forming an outer layer on the metal layer configured to provide a non-bonding surface for the bumped contact;

forming a plurality of leads in the metal layer configured to electrically engage and support the bumped contact, each lead including at least one blade; and

forming a recess in the substrate such that the leads are cantilevered over the recess and are configured to move within the recess during electrical engagement of the bumped contact.

40. (previously presented) The method of claim 39 wherein the outer layer comprises a conductive polymer.

41. (previously presented) The method of claim 39 wherein the outer layer comprises a material selected from the group consisting of a carbon film and a metal filled silicone.

Claim 42 (Withdrawn)

43. (previously presented) The method of claim 39 further comprising forming a connecting segment on the substrate electrically connecting the leads, a conductive via in the substrate in electrical communication with the connecting segment and a contact on the substrate in electrical communication with the conductive via.

Claims 44-48 (Withdrawn)

49. (previously presented) A method for fabricating an interconnect for engaging bumped contacts on a semiconductor component comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of interconnect contacts on the substrate configured to electrically engage the bumped

contacts, each interconnect contact comprising a recess in the surface and a plurality of leads cantilevered over the recess configured to support a bumped contact for movement in the recess; and

forming an outer layer on each lead configured to provide non-bonding surfaces for the bumped contacts.

50. (previously presented) The method of claim 49 wherein the outer layer comprises a conductive polymer.

51. (previously presented) The method of claim 49 further comprising forming at least one blade on each lead configured to penetrate a bumped contact.

52-58. (Withdrawn)

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Conclude*